

/ Descriptions

TO-252

NPN

Silicon NPN transistor in a TO-252 Plastic Package.

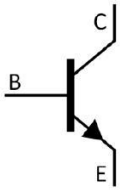
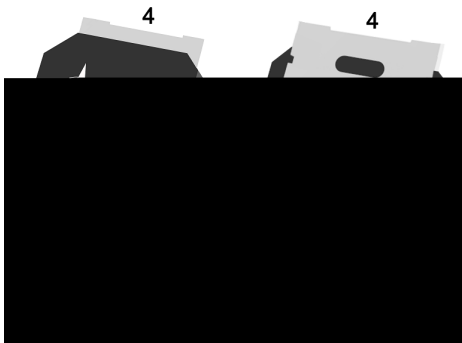
/ Features

AEC-Q101

High collector-Emitter breakdown voltage, Suitable for transformer, Qualified to AEC-Q101 Standards for High Reliability, HF Product.

/ Applications

High voltage general purpose applications, Meet the stringent requirements of automotive applications.

/ Equivalent Circuit**/ Pinning**

PIN1 Base

PIN 2,4 Collector

PIN 3 Emitter

/ h_{FE} Classifications & Marking

See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	300	V
Collector to Emitter Voltage	V_{CEO}	300	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	500	mA
Collector Power Dissipation	P_C	1.56	W
Collector Power Dissipation	$P_C(T_C=25^\circ\text{C})$	15	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ
-----------	--------	-----------------	-----	-----

/ Electrical Characteristic Curve

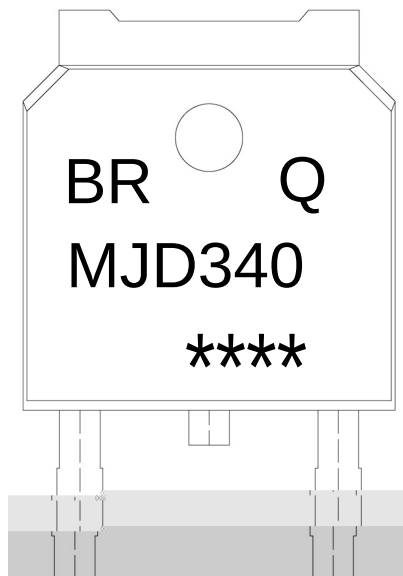


单位: mm

Dimerization In Maltotetraose			Dimerization In Maltotriose		
Min.	Max.	Mean	Min.	Max.	Mean
5.20	6.25	5.73	2.20	2.40	2.30
2.34	0.95	1.25	2.74	0.79	0.90
9.85	10.35	10.10	0.45	0.55	0.50
0.45	0.55	0.50	1.70	2.00	1.85
6.45	6.75	6.60	0.60	0.60	0.60

T0-252

/ Marking Instructions



BR

Q

MJD340

Note:

BR: Company Code

Q: Automobile halogen-free product Code

MJD340: Product Type

****: Lot No. Code, code change with Lot No

BRMJD340Q

Rev.B Apr.-2023



蓝箭电子
BLUE ROCKET ELECTRONICS

DATA SHEET